

74HC366; 74HCT366

Hex buffer/line driver; 3-state; inverting

Rev. 03 — 21 November 2006

Product data sheet

1. General description

The 74HC366; 74HCT366 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL).

The 74HC366; 74HCT366 has six inverting buffer/line drivers with 3-state outputs. The 3-state outputs (\overline{nY}) are controlled by the output enable inputs ($\overline{OE1}$, $\overline{OE2}$). A HIGH on \overline{OEn} causes the outputs to assume a high-impedance OFF-state.

The 74HC366; 74HCT366 is functionally identical to:

- 74HC365; 74HCT365, but has inverted outputs

2. Features

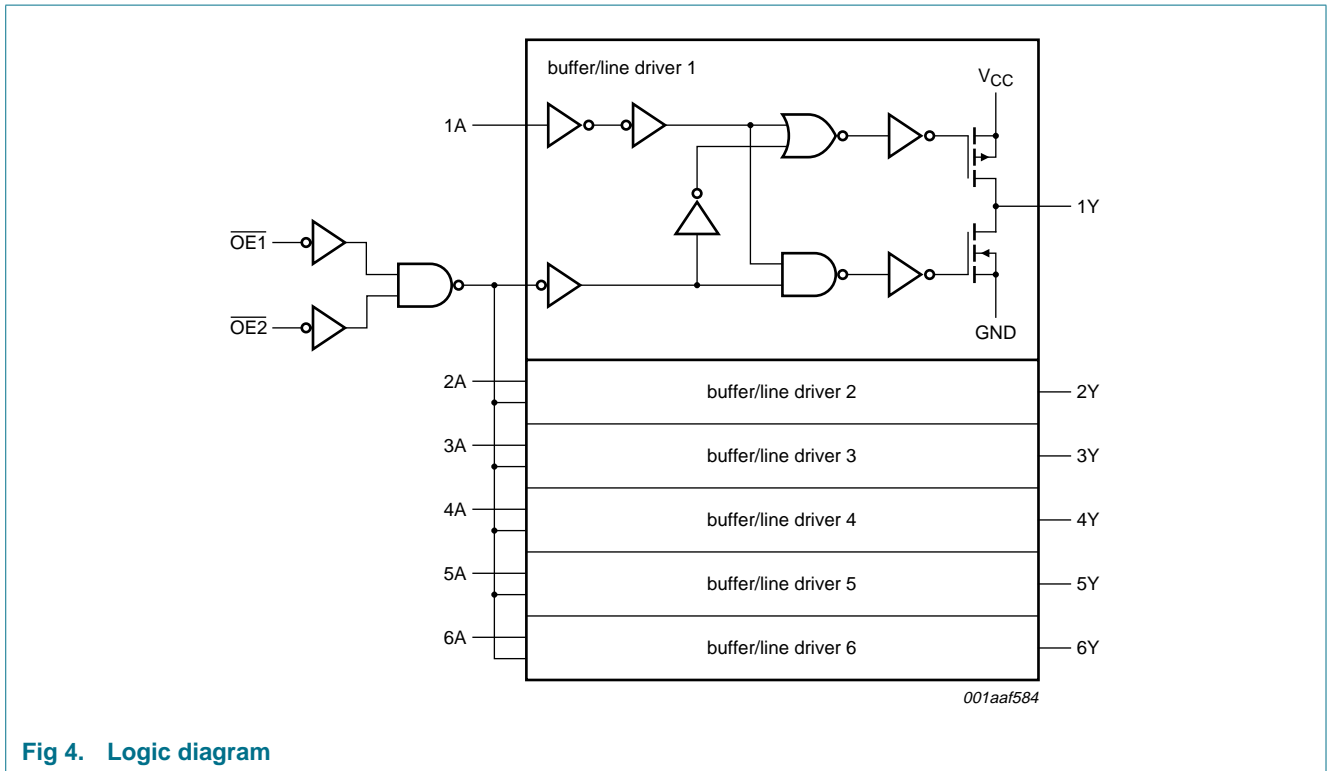
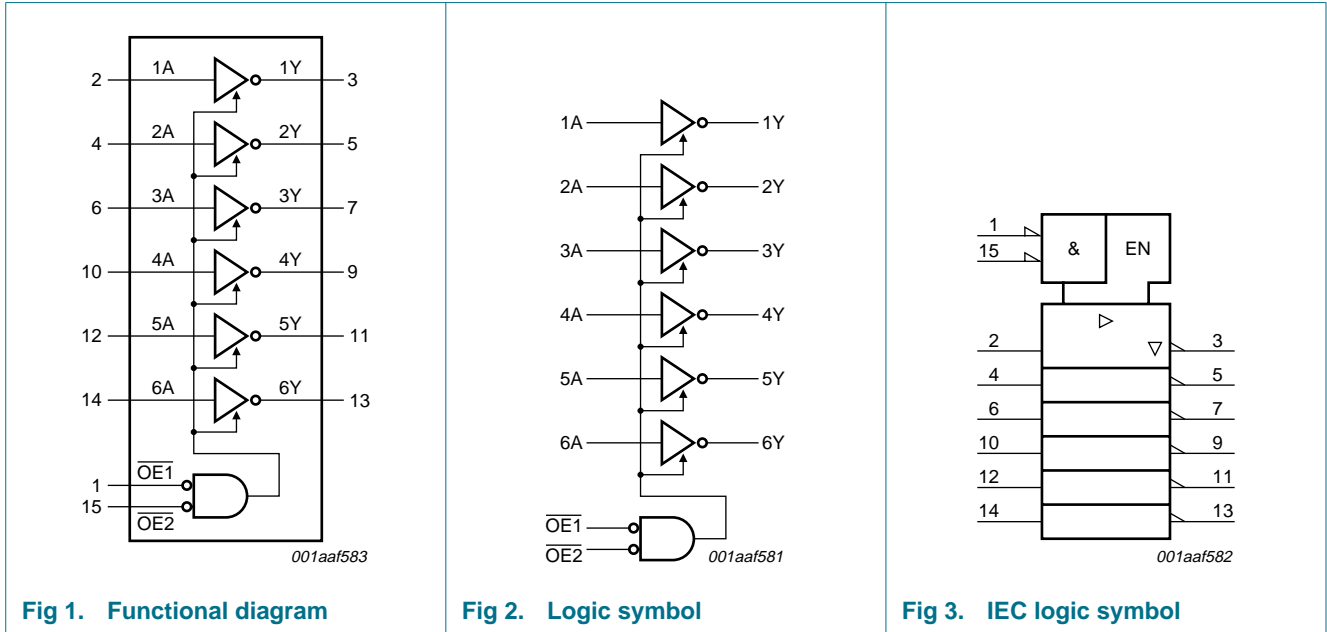
- Inverting outputs
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM EIA/JESD22-A114-D exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

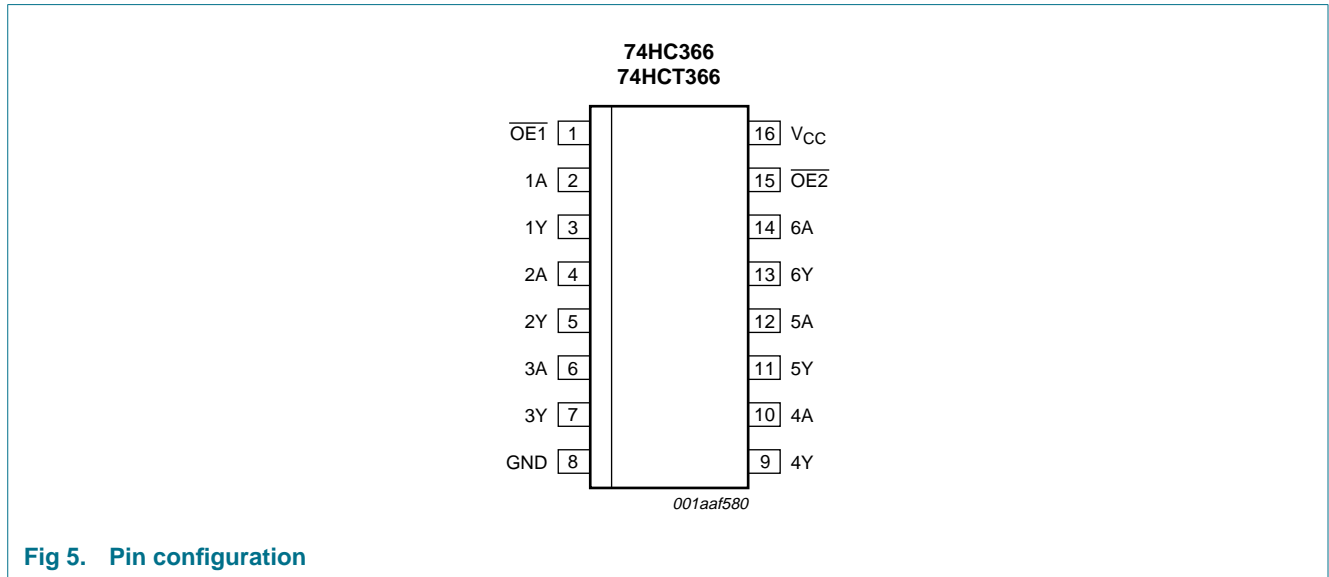
Type number	Package			Version
	Temperature range	Name	Description	
74HC366				
74HC366D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HC366N	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DIP16	plastic dual in-line package; 16 leads (300 mil); long body	SOT38-1
74HC366PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74HCT366				
74HCT366D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT366DB	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT366N	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DIP16	plastic dual in-line package; 16 leads (300 mil); long body	SOT38-1
74HCT366PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
OE1	1	output enable input 1 (active LOW)
1A	2	data input 1
1Y	3	data output 1
2A	4	data input 2
2Y	5	data output 2
3A	6	data input 3
3Y	7	data output 3
GND	8	ground (0 V)
4Y	9	data output 4
4A	10	data input 4
5Y	11	data output 5
5A	12	data input 5
6Y	13	data output 6
6A	14	data input 6
OE2	15	output enable input 2 (active LOW)
V _{CC}	16	supply voltage

6. Functional description

Table 3. Function table^[1]

Control		Input	Output
OE1	OE2	nA	nY
L	L	L	H
L	L	H	L
X	H	X	Z
H	X	X	Z

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit	
V _{CC}	supply voltage		-0.5	+7	V	
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	-	±20	mA	
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	-	±20	mA	
I _O	output current	V _O = -0.5 V to (V _{CC} + 0.5 V)	-	±35	mA	
I _{CC}	supply current		-	70	mA	
I _{GND}	ground current		-	-70	mA	
T _{stg}	storage temperature		-65	+150	°C	
P _{tot}	total power dissipation	DIP16 package	[1]	-	750	mW
		SO16 package	[2]	-	500	mW
		SSOP16 package	[3]	-	500	mW
		TSSOP16 package	[3]	-	500	mW

- [1] For DIP16 package: P_{tot} derates linearly with 12 mW/K above 70 °C.
 [2] For SO16 package: P_{tot} derates linearly with 8 mW/K above 70 °C.
 [3] For SSOP16 and TSSOP16 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74HC366						
V _{CC}	supply voltage		2.0	5.0	6.0	V
V _I	input voltage		0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C

Table 5. Recommended operating conditions ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _r	rise time	inputs				
		V _{CC} = 2.0 V	-	-	1000	ns
		V _{CC} = 4.5 V	-	6.0	500	ns
		V _{CC} = 6.0 V	-	-	400	ns
t _f	fall time	inputs				
		V _{CC} = 2.0 V	-	-	1000	ns
		V _{CC} = 4.5 V	-	6.0	500	ns
		V _{CC} = 6.0 V	-	-	400	ns
74HCT366						
V _{CC}	supply voltage		4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
t _r	rise time	inputs; V _{CC} = 4.5 V	-	6.0	500	ns
t _f	fall time	inputs; V _{CC} = 4.5 V	-	6.0	500	ns

9. Static characteristics

Table 6. Static characteristics 74HC366

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}	-	-	-	
		I _O = -20 μA; V _{CC} = 2.0 V	1.9	2.0	-	V
		I _O = -20 μA; V _{CC} = 4.5 V	4.4	4.5	-	V
		I _O = -20 μA; V _{CC} = 6.0 V	5.9	6.0	-	V
		I _O = -6.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	V
		I _O = -7.8 mA; V _{CC} = 6.0 V	5.48	5.81	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	0.16	0.26	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	μA

Table 6. Static characteristics 74HC366 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	± 0.5	μ A
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	8.0	μ A
C_I	input capacitance		-	3.5	-	pF
$T_{amb} = -40$ °C to $+85$ °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 2.0$ V	1.5	-	-	V
		$V_{CC} = 4.5$ V	3.15	-	-	V
		$V_{CC} = 6.0$ V	4.2	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 2.0$ V	-	-	0.5	V
		$V_{CC} = 4.5$ V	-	-	1.35	V
		$V_{CC} = 6.0$ V	-	-	1.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20$ μ A; $V_{CC} = 2.0$ V	1.9	-	-	V
		$I_O = -20$ μ A; $V_{CC} = 4.5$ V	4.4	-	-	V
		$I_O = -20$ μ A; $V_{CC} = 6.0$ V	5.9	-	-	V
		$I_O = -6.0$ mA; $V_{CC} = 4.5$ V	3.84	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20$ μ A; $V_{CC} = 2.0$ V	-	-	0.1	V
		$I_O = 20$ μ A; $V_{CC} = 4.5$ V	-	-	0.1	V
		$I_O = 20$ μ A; $V_{CC} = 6.0$ V	-	-	0.1	V
		$I_O = 6.0$ mA; $V_{CC} = 4.5$ V	-	-	0.33	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V;	-	-	± 1.0	μ A
		$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	± 5.0	μ A
		$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	80	μ A
		$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V;	-	-	± 1.0	μ A
		$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	± 5.0	μ A
$T_{amb} = -40$ °C to $+125$ °C						
V_{IH}	HIGH-level input voltage	$V_{CC} = 2.0$ V	1.5	-	-	V
		$V_{CC} = 4.5$ V	3.15	-	-	V
		$V_{CC} = 6.0$ V	4.2	-	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 2.0$ V	-	-	0.5	V
		$V_{CC} = 4.5$ V	-	-	1.35	V
		$V_{CC} = 6.0$ V	-	-	1.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20$ μ A; $V_{CC} = 2.0$ V	1.9	-	-	V
		$I_O = -20$ μ A; $V_{CC} = 4.5$ V	4.4	-	-	V
		$I_O = -20$ μ A; $V_{CC} = 6.0$ V	5.9	-	-	V
		$I_O = -6.0$ mA; $V_{CC} = 4.5$ V	3.7	-	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20$ μ A; $V_{CC} = 2.0$ V	-	-	0.1	V
		$I_O = 20$ μ A; $V_{CC} = 4.5$ V	-	-	0.1	V
		$I_O = 20$ μ A; $V_{CC} = 6.0$ V	-	-	0.1	V
		$I_O = 6.0$ mA; $V_{CC} = 4.5$ V	-	-	0.33	V

Table 6. Static characteristics 74HC366 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 μA; V _{CC} = 2.0 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	-	0.4	V
		I _O = 7.8 mA; V _{CC} = 6.0 V	-	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±1.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±10.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	160	μA

Table 7. Static characteristics 74HCT366

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = -20 μA	4.4	4.5	-	V
		I _O = -6.0 mA	3.98	4.32	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 μA	-	0	0.1	V
		I _O = 6.0 mA	-	0.16	0.26	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND per input pin; other inputs at GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V	-	-	±0.5	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	μA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 2.1 V; other inputs at V _{CC} or GND; I _O = 0 A				
		pins nA	-	100	360	μA
		pin $\overline{OE1}$	-	100	360	μA
		pin $\overline{OE2}$	-	90	320	μA
C _I	input capacitance		-	3.5	-	pF
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = -20 μA	4.4	-	-	V
		I _O = -6.0 mA	3.84	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 μA	-	-	0.1	V
		I _O = 6.0 mA	-	-	0.33	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±1.0	μA

Table 7. Static characteristics 74HCT366 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND per input pin; other inputs at GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V			±5.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	80	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 2.1 V; other inputs at V _{CC} or GND; I _O = 0 A				
		pins nA	-	-	450	µA
		pin $\overline{OE1}$	-	-	450	µA
		pin $\overline{OE2}$	-	-	400	µA
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = -20 µA	4.4	-	-	V
		I _O = -6.0 mA	3.7	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 µA	-	-	0.1	V
		I _O = 6.0 mA	-	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±1.0	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND per input pin; other inputs at GND or V _{CC} ; I _O = 0 A; V _{CC} = 5.5 V	-	-	±10.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	160	µA
ΔI _{CC}	additional supply current	V _I = V _{CC} - 2.1 V; other inputs at V _{CC} or GND; I _O = 0 A				
		pins nA	-	-	490	µA
		pin $\overline{OE1}$	-	-	490	µA
		pin $\overline{OE2}$	-	-	441	µA

10. Dynamic characteristics

Table 8. Dynamic characteristics 74HC366

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; see test circuit [Figure 8](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
t _{pd}	propagation delay	nA to nY; see Figure 6	[1]			
		V _{CC} = 2.0 V	-	33	100	ns
		V _{CC} = 4.5 V	-	12	20	ns
		V _{CC} = 5 V; C _L = 15 pF	-	10	-	ns
		V _{CC} = 6.0 V	-	10	17	ns
t _{en}	enable time	$\overline{OE}n$ to nY; see Figure 7	[2]			
		V _{CC} = 2.0 V	-	44	150	ns
		V _{CC} = 4.5 V	-	16	30	ns
		V _{CC} = 6.0 V	-	13	26	ns

Table 8. Dynamic characteristics 74HC366 ...continued

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; see test circuit [Figure 8](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t _{dis}	disable time	\overline{OEn} to nY; see Figure 7	[3]			
		V _{CC} = 2.0 V	-	55	150	ns
		V _{CC} = 4.5 V	-	20	30	ns
		V _{CC} = 6.0 V	-	16	26	ns
t _t	transition time	see Figure 6	[4]			
		V _{CC} = 2.0 V	-	14	60	ns
		V _{CC} = 4.5 V	-	5	12	ns
		V _{CC} = 6.0 V	-	4	10	ns
C _{PD}	power dissipation capacitance	per buffer; V _I = GND to V _{CC}	[5]	-	30	pF
T_{amb} = -40 °C to +85 °C						
t _{pd}	propagation delay	nA to nY; see Figure 6	[1]			
		V _{CC} = 2.0 V	-	-	125	ns
		V _{CC} = 4.5 V	-	-	25	ns
		V _{CC} = 6.0 V	-	-	21	ns
t _{en}	enable time	\overline{OEn} to nY; see Figure 7	[2]			
		V _{CC} = 2.0 V	-	-	190	ns
		V _{CC} = 4.5 V	-	-	38	ns
		V _{CC} = 6.0 V	-	-	33	ns
t _{dis}	disable time	\overline{OEn} to nY; see Figure 7	[3]			
		V _{CC} = 2.0 V	-	-	190	ns
		V _{CC} = 4.5 V	-	-	38	ns
		V _{CC} = 6.0 V	-	-	33	ns
t _t	transition time	see Figure 6	[4]			
		V _{CC} = 2.0 V	-	-	75	ns
		V _{CC} = 4.5 V	-	-	15	ns
		V _{CC} = 6.0 V	-	-	13	ns
T_{amb} = -40 °C to +125 °C						
t _{pd}	propagation delay	nA to nY; see Figure 6	[1]			
		V _{CC} = 2.0 V	-	-	150	ns
		V _{CC} = 4.5 V	-	-	30	ns
		V _{CC} = 6.0 V	-	-	26	ns
t _{en}	enable time	\overline{OEn} to nY; see Figure 7	[2]			
		V _{CC} = 2.0 V	-	-	225	ns
		V _{CC} = 4.5 V	-	-	45	ns
		V _{CC} = 6.0 V	-	-	38	ns
t _{dis}	disable time	\overline{OEn} to nY; see Figure 7	[3]			
		V _{CC} = 2.0 V	-	-	225	ns
		V _{CC} = 4.5 V	-	-	45	ns
		V _{CC} = 6.0 V	-	-	38	ns

Table 8. Dynamic characteristics 74HC366 ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; see test circuit [Figure 8](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_t	transition time	see Figure 6	[4]			
		$V_{CC} = 2.0$ V	-	-	90	ns
		$V_{CC} = 4.5$ V	-	-	18	ns
		$V_{CC} = 6.0$ V	-	-	15	ns

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [2] t_{en} is the same as t_{PZH} and t_{PZL} .
- [3] t_{dis} is the same as t_{PHZ} and t_{PLZ} .
- [4] t_t is the same as t_{THL} and t_{TLH} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

Table 9. Dynamic characteristics 74HCT366

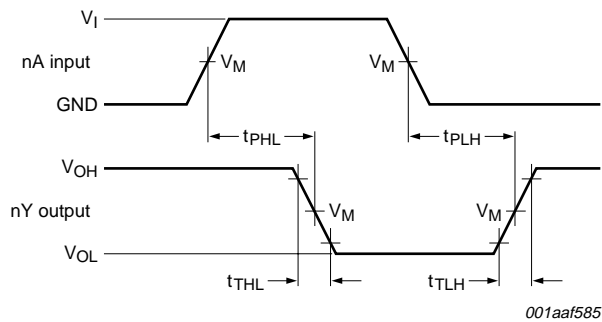
Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; see test circuit [Figure 8](#).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$T_{amb} = 25$ °C							
t_{pd}	propagation delay	nA to nY; see Figure 6	[1]				
		$V_{CC} = 4.5$ V	-	13	24	ns	
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	11	-	ns	
t_{en}	enable time	\overline{OEn} to nY; $V_{CC} = 4.5$ V; see Figure 7	[2]	-	16	35	ns
t_{dis}	disable time	\overline{OEn} to nY; $V_{CC} = 4.5$ V; see Figure 7	[3]	-	20	35	ns
t_t	transition time	$V_{CC} = 4.5$ V; see Figure 6	[4]	-	5	12	ns
C_{PD}	power dissipation capacitance	per buffer; $V_I = GND$ to $(V_{CC} - 1.5$ V)	[5]	-	30	-	pF
$T_{amb} = -40$ °C to $+85$ °C							
t_{pd}	propagation delay	nA to nY; $V_{CC} = 4.5$ V; see Figure 6	[1]	-	-	30	ns
t_{en}	enable time	\overline{OEn} to nY; $V_{CC} = 4.5$ V; see Figure 7	[2]	-	-	44	ns
t_{dis}	disable time	\overline{OEn} to nY; $V_{CC} = 4.5$ V; see Figure 7	[3]	-	-	44	ns
t_t	transition time	$V_{CC} = 4.5$ V; see Figure 6	[4]	-	-	15	ns
$T_{amb} = -40$ °C to $+125$ °C							
t_{pd}	propagation delay	nA to nY; $V_{CC} = 4.5$ V; see Figure 6	[1]	-	-	36	ns
t_{en}	enable time	\overline{OEn} to nY; $V_{CC} = 4.5$ V; see Figure 7	[2]	-	-	53	ns
t_{dis}	disable time	\overline{OEn} to nY; $V_{CC} = 4.5$ V; see Figure 7	[3]	-	-	53	ns
t_t	transition time	$V_{CC} = 4.5$ V; see Figure 6	[4]	-	-	18	ns

- [1] t_{pd} is the same as t_{PHL} and t_{PLH} .
- [2] t_{en} is the same as t_{PZH} and t_{PZL} .
- [3] t_{dis} is the same as t_{PHZ} and t_{PLZ} .

- [4] t_t is the same as t_{THL} and t_{TLH} .
- [5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 $\sum(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

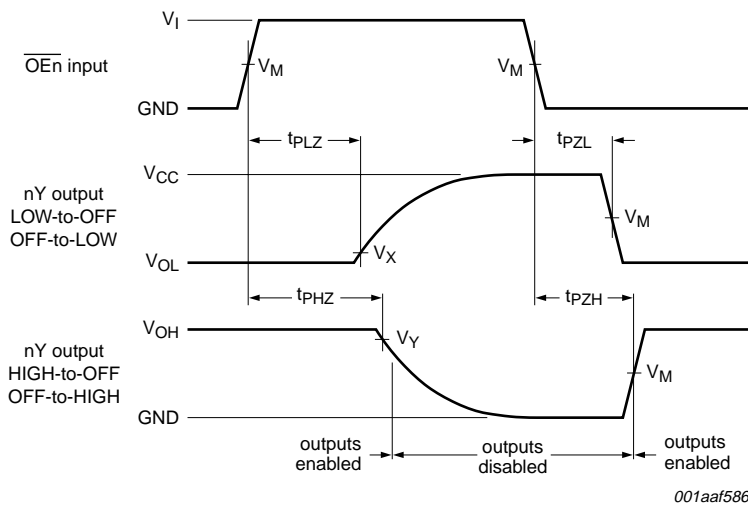
11. Waveforms



Measurement points are given in [Table 10](#).

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 6. Propagation delay data input (nA) to output (nY) and output transition time



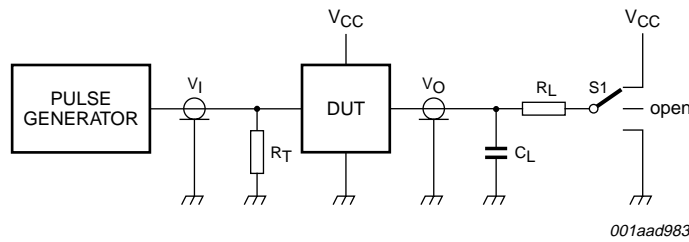
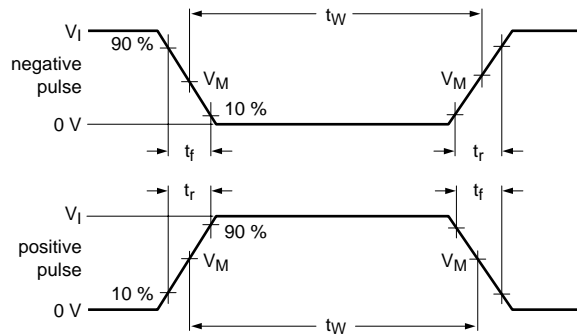
Measurement points are given in [Table 10](#).

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 7. 3-state enable and disable times

Table 10. Measurement points

Type	Input		Output	
	V_M	V_M	V_X	V_Y
74HC366	$0.5V_{CC}$	$0.5V_{CC}$	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$
74HCT366	1.3 V	1.3 V	$0.1 \times V_{CC}$	$0.9 \times V_{CC}$



Test data is given in [Table 11](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

C_L = Load capacitance including jig and probe capacitance

R_L = Load resistor

S1 = Test selection switch

Fig 8. Load circuitry for measuring switching times

Table 11. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC366	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74HCT366	3 V	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1

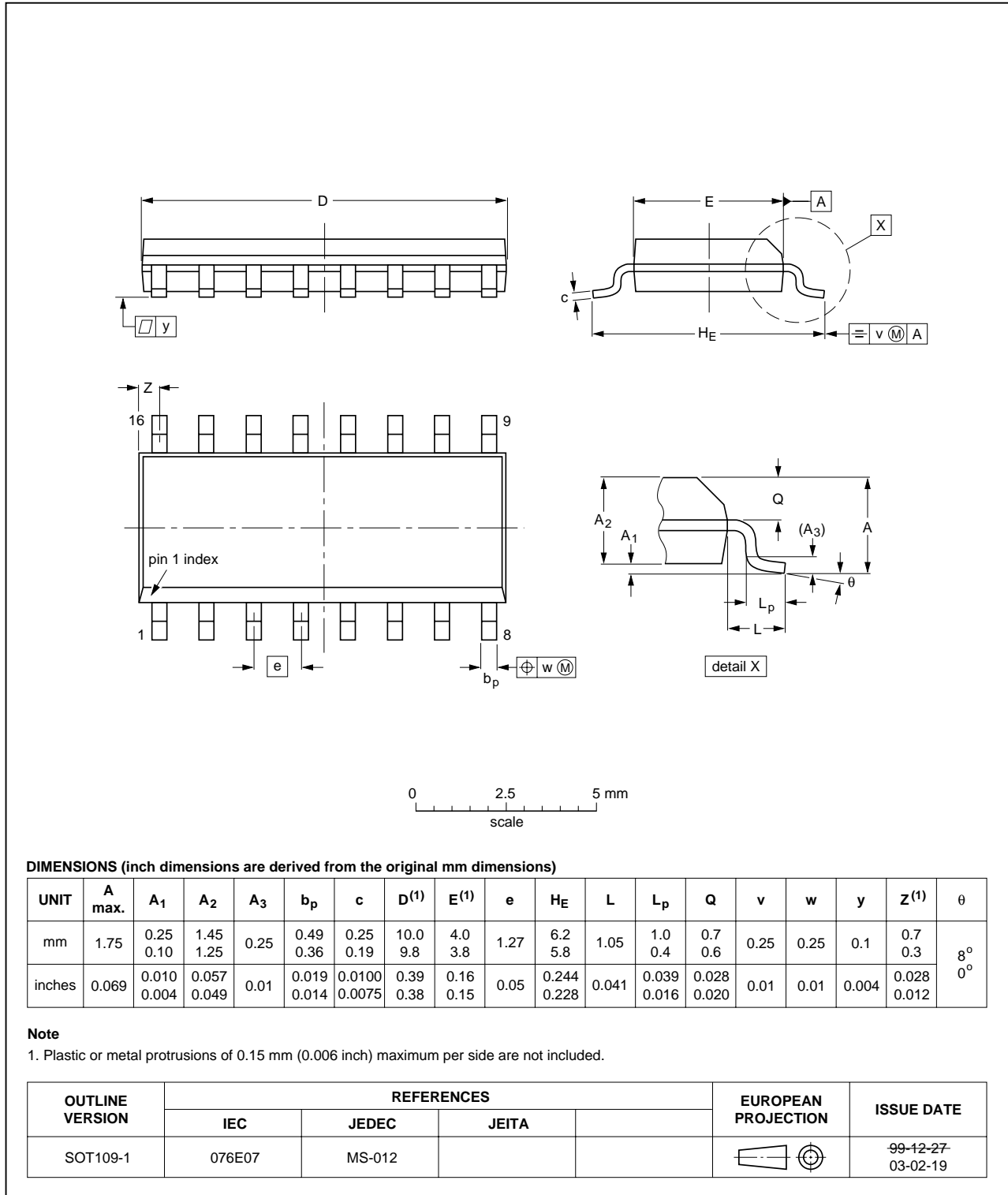


Fig 9. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

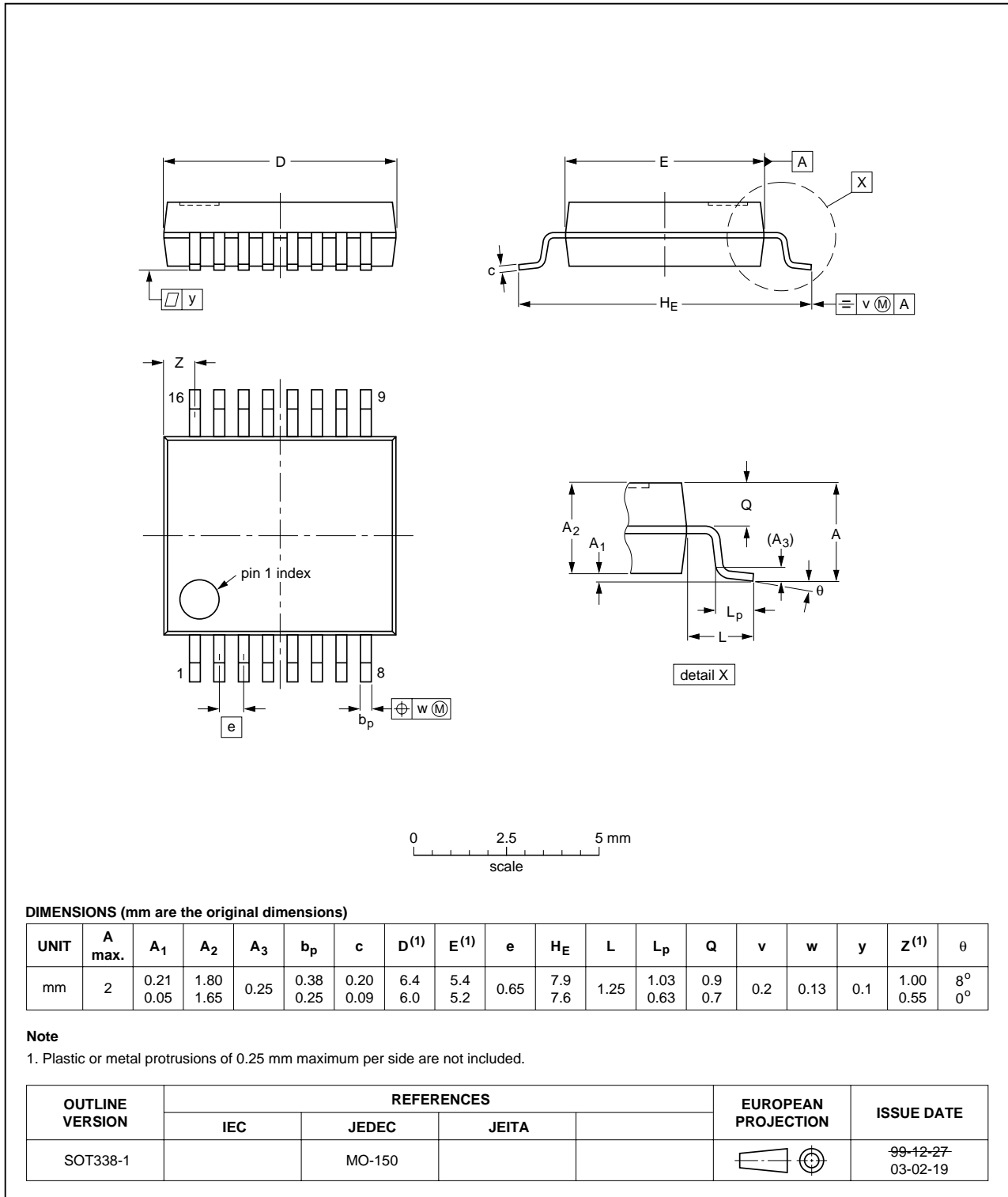


Fig 10. Package outline SOT338-1 (SSOP16)

DIP16: plastic dual in-line package; 16 leads (300 mil); long body

SOT38-1

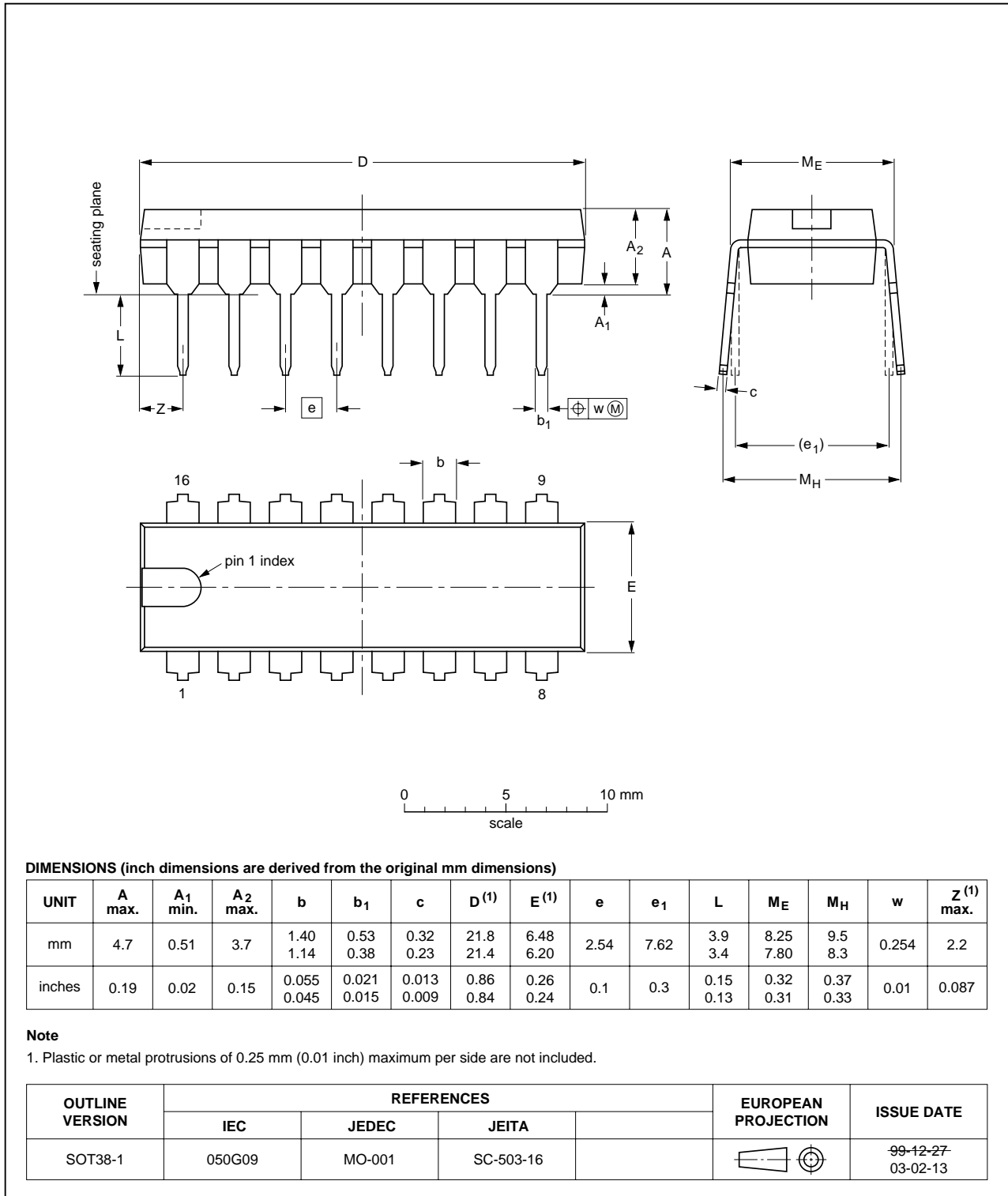


Fig 11. Package outline SOT38-1 (DIP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

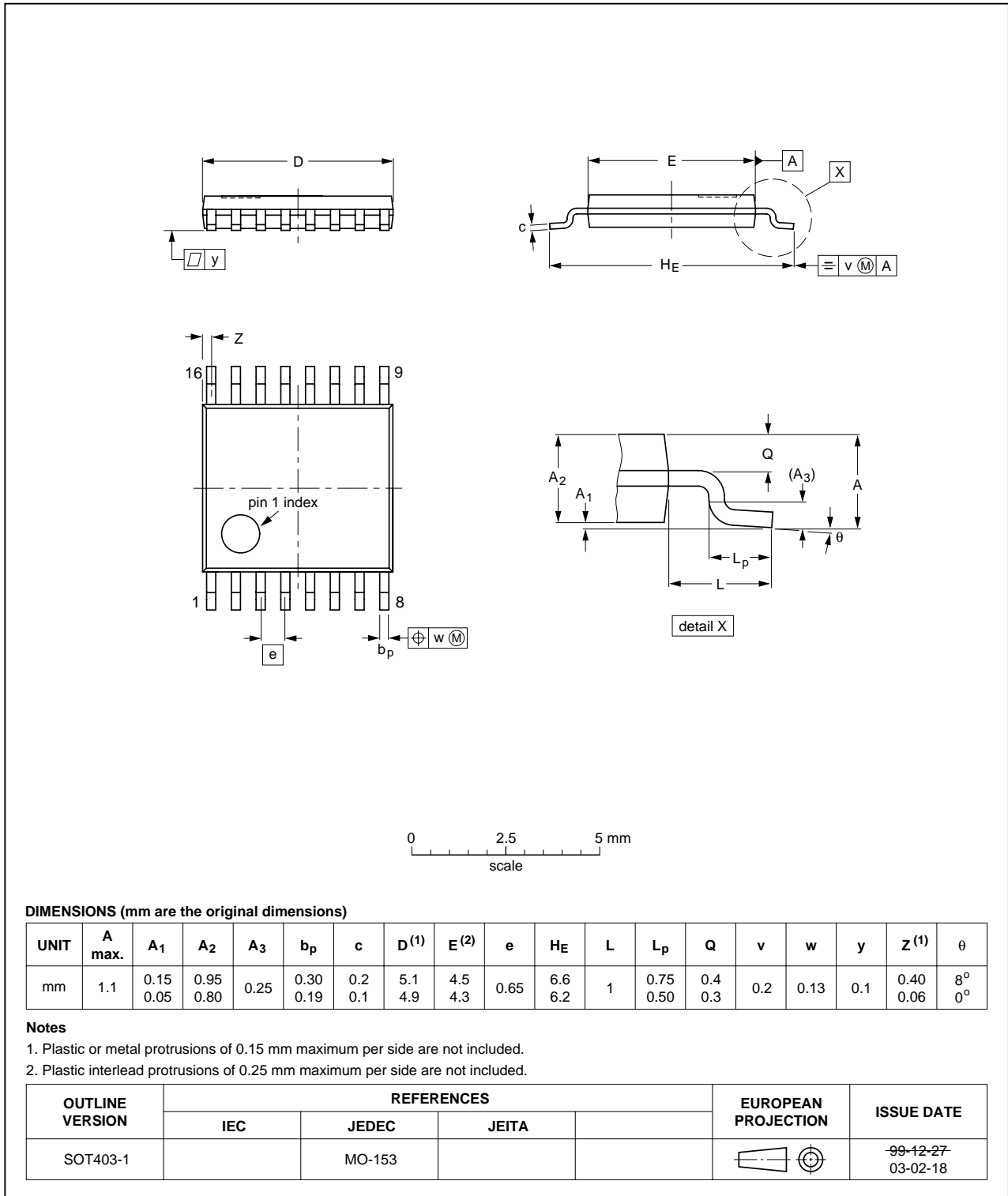


Fig 12. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 12. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT366_3	20061121	Product data sheet	-	74HC_HCT366_CNV_2
Modifications:		<ul style="list-style-type: none">• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors• Legal texts have been adapted to the new company name where appropriate• Added family specification		
74HC_HCT366_CNV_2	19901201	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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